



YETDA INDUSTRY LTD.

**Infrared Emitting Diode
RT5-1337ET-B**

Absolute Maximum Ratings (Ta = 25°C) :

Characteristic	Symbol	Rating	Unit
Pulse forward current($t \leq 10\mu s$)	IMP	1	A
Forward direct current	IFM	100	mA
Reverse voltage	VRM	5	V
Operating temperature	Topr	-25 TO +75	°C
Storage temperature	Tstg	-25 TO +100	°C
Power dissipation	Pd	200	mW

Lead Soldering Temperature (5mm from body) 260°C for 3sec.

Electro-Optical Characteristics (Ta = 25°C)

Characteristic	Condition	Symbol	Min.	Typ.	Max.	Unit
Radiant intensity	IF=50mA	Ie	20	40		mW/sr
Forward voltage	IF=100mA	VF		1.6	2.0	V
Reverse current	VR=4V	IR			10	uA
Peak emission wavelength	IF=50mA	λp		850		nm
Spectral band width @ 50%	IF=50mA	$\Delta \lambda$		42		nm
Reverse breakdown voltage	IR=100uA	BVR	5	30		V
Junction capacitance	VR=0V, f=1MHz	Co		32		pF
Rise time/Fall time	IF=50mA	Tr/tf		30/15		ns
Viewing angle	IF=50mA	2θ		40		deg.

Package

Item:500

